SΒ	Roll	No
J.D.	NOII	INU

	ELECTRONICS -I 3 RD Exam/Elect/0525/0252/Nov'2016		
Duration: 3 hrs M. Marks			
	SECTION A		
Q:1	Fill in the blanks:- 15x1=15		
a	The process of adding impurities is called		
	The unit of inductance is		
C.	The turn on voltage of Germanium diode is volt.		
d	LED stands for		
е	Usually, a zener diode is used as a		
f.			
	The opposition to the flow of current in a.c. source is called		
h	Resistivity of semi conductors lies between and		
i.			
	The max. efficiency of full wave rectifier is		
	The capacitor circuit does not allow to pass component.		
l.	· ————		
	i diode has a negative resistance.		
	The biasing is most widely used.		
0	region of the transistor is the best place for operating point.		
	SECTION B		
NOTE	:- Attempt any five questions: 5x6=30		
Q:2	a) Classify different types of materials on the basis of Energy band diagram.		
	b) Describe the working of PNP transistor.		
	c) Describe the working of a FULL wave rectifier.		
	d) How does temperature effect the conductivity of an intrinsic semiconductor?		
	e) Write a short note on PN- junction. Draw its V-I characteristics.		
	f) Explain zener diode as voltage regulator.		
	g) Discuss the advantages of FET over conventional transistor.		
	h) What is faithful amplification? Explain in brief.		
	SECTION C		
NOTE	:- Attempt any three questions: 3x10=30		
Q 3:	Sketch output characteristics curve for NPN transistor in CB configuration and also indicate		
	active, cut-off, saturation regions.		
Q 4:	Draw circuit diagram of HALF wave bridge rectifier and explain its working with the help of a input and output waveforms.		
Q5:	Write a note on various types of Filters in detail.		
Q 6:	Explain R-C coupled amplifier with the help of circuit diagram. Draw its gain versus frequency characteristics and indicate cut-off frequency and band width.		

Q 7: Explain the construction, working of $\,$ JFET with suitable diagram.